WHAT IS CLAIMED IS:

1. A semiconductor laser having a laser beam-emitting end facet including a laser beam-emitting region, the semiconductor laser comprising a three-dimensional feature portion indicating the location of the light-emitting region formed on the laser beam-emitting end facet at a region different from the light emitting region.

2. The semiconductor laser as claimed in claim 1, wherein the three-dimensional feature portion is at least one of a concavity and a convexity formed on the laser beam-emitting end facet at a region different from the light-emitting region.

3. The semiconductor laser as claimed in claim 1, further comprising a light-shielding film covering at least the light-emitting region, the light-shielding film being formed with a small opening at part of the portion over the light-emitting region.

4. The semiconductor laser as claimed in claim 2, further comprising a light-shielding film covering at least the light-emitting region, the light-shielding film being formed with a small opening at part of the portion over the light-emitting region.

5. The semiconductor laser as claimed in claim 3, wherein the light-shielding film further covers the three-dimensional feature portion.

6. The semiconductor laser as claimed in claim 3, further comprising a dielectric film provided between the laser beam-emitting end facet and the light-shielding film, part of the dielectric film being exposed at the small opening.

7. The semiconductor laser as claimed in claim 4, further comprising a dielectric film provided between the laser beam-emitting end facet and the light-shielding film, part of the dielectric film being exposed at the small opening.

8. A method of producing a semiconductor laser having a laser beam-emitting end facet including a laser beam-emitting region comprising a step of forming a three-dimensional feature portion at a location on the laser beam-emitting end facet to have a prescribed relationship with the light-emitting region.

9. The method as claimed in claim 8, further comprising a step of forming a light-shielding film covering at least the light-emitting region and a step of forming the light-shielding film with a small opening at a location having a prescribed positional relationship with the three-dimensional feature portion.

10. The method as claimed in claim 9, wherein the step of forming the three-dimensional feature portion and the step of forming the small opening both utilize focused ion beam processing.

11. The method as claimed in claim 8, further comprising a step of irradiating at least the light-emitting region of the laser beam-emitting end facet with a focused ion beam before the step of forming the three-dimensional feature portion.

12. The method as claimed in claim 9, further comprising a step of irradiating at least the light-emitting region of the laser beam-emitting end facet with a focused ion beam before the step of forming the three-dimensional feature portion.

13. The method as claimed in claim 10, further comprising a step of irradiating at least the light-emitting region of the laser beam-emitting end facet with a focused ion beam before the step of forming the three-dimensional feature portion.

14. An evanescent optical head for reading/writing of data from/to a recording medium using evanescent light, the evanescent optical head being equipped with a semiconductor

laser for emitting the evanescent light that has a laser beam-emitting end facet including a light-emitting region and comprises a three-dimensional feature portion formed on the laser beam-emitting end facet, a light shielding film covering at least the light-emitting region, and a small opening for emitting the evanescent light formed in the light-shielding film at a location to have a prescribed positional relationship with the three-dimensional feature portion.